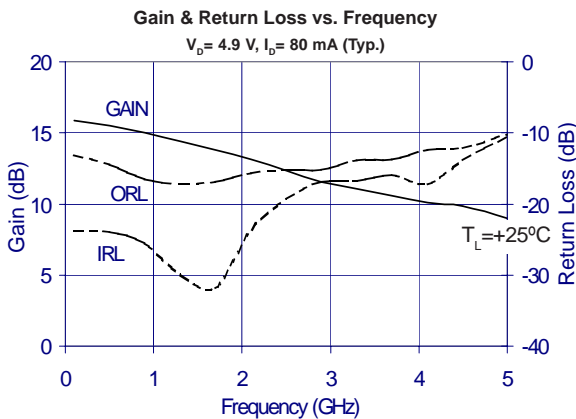


The SGA-6386 is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring 1 micron emitters provides high  $F_T$  and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only 2 DC-blocking capacitors, a bias resistor and an optional RF choke are required for operation.

The matte tin finish on Sirenza's lead-free package utilizes a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. This package is also manufactured with green molding



## SGA-6386

**SGA-6386Z**  RoHS Compliant & Green Package

**DC-5000 MHz, Cascadable SiGe HBT MMIC Amplifier**



### Product Features

- Now available in Lead Free, RoHS Compliant, & Green Packaging
- Broadband Operation: DC-5000 MHz
- Cascadable 50 Ohm
- Operates From Single Supply
- Low Thermal Resistance Package

### Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

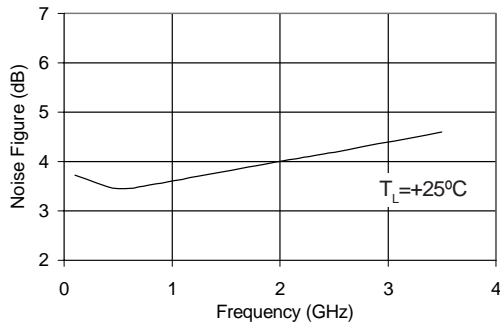
Symbol	Parameter	Units	Frequency	Min.	Typ.	Max.
G	Small Signal Gain	dB	850 MHz 1950 MHz 2400 MHz	14.0	15.4 13.5 12.5	16.9
$P_{1dB}$	Output Power at 1dB Compression	dBm	850 MHz 1950 MHz		21.0 19.0	
$OIP_3$	Output Third Order Intercept Point	dBm	850 MHz 1950 MHz		36.0 34.0	
Bandwidth	Determined by Return Loss (>10dB)	MHz			5000	
IRL	Input Return Loss	dB	1950 MHz		26.7	
ORL	Output Return Loss	dB	1950 MHz		16.2	
NF	Noise Figure	dB	1950 MHz		4.0	
$V_D$	Device Operating Voltage	V		4.6	4.9	5.4
$I_D$	Device Operating Current	mA		72	80	88
$R_{TH}$ , j-l	Thermal Resistance (junction to lead)	$^\circ\text{C/W}$			97	
<b>Test Conditions:</b> $V_S = 8\text{v}$ $I_D = 80\text{mA Typ.}$ $OIP3$ Tone Spacing = 1 MHz, $P_{out}$ per tone = 0 dBm $R_{BIAS} = 39\text{ Ohms}$ $T_L = 25^\circ\text{C}$ $Z_S = Z_L = 50\text{ Ohms}$						

**Typical RF Performance at Key Operating Frequencies**

Symbol	Parameter	Unit	Frequency (MHz)					
			100	500	850	1950	2400	3500
G	Small Signal Gain	dB	15.9	15.5	15.4	13.5	12.5	10.7
OIP <sub>3</sub>	Output Third Order Intercept Point	dBm	37.1	37.1	36.0	34.0	32.2	27.9
P <sub>1dB</sub>	Output Power at 1dB Compression	dBm	20.2	20.5	21.0	19.0	18.6	16.3
IRL	Input Return Loss	dB	23.8	23.9	25.6	26.7	20.4	16.0
ORL	Output Return Loss	dB	13.2	14.5	16.6	16.2	15.1	14.2
S <sub>12</sub>	Reverse Isolation	dB	20.0	20.2	20.4	19.9	19.2	17.2
NF	Noise Figure	dB	3.7	3.4	3.6	4.0	4.2	4.6

Test Conditions:  $V_S = 8V$        $I_D = 80mA$  Typ.      OIP3 Tone Spacing = 1 MHz, Pout per tone = 0 dBm  
 $R_{BIAS} = 39$  Ohms       $T_L = 25^\circ C$        $Z_S = Z_L = 50$  Ohms

**Noise Figure vs. Frequency**  
 $V_D = 4.9 V, I_D = 80 mA$



**Absolute Maximum Ratings**

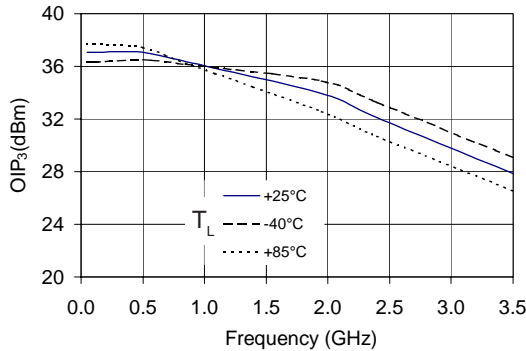
Parameter	Absolute Limit
Max. Device Current ( $I_D$ )	160 mA
Max. Device Voltage ( $V_D$ )	7 V
Max. RF Input Power	+18 dBm
Max. Junction Temp. ( $T_J$ )	+150°C
Operating Temp. Range ( $T_L$ )	-40°C to +85°C
Max. Storage Temp.	+150°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

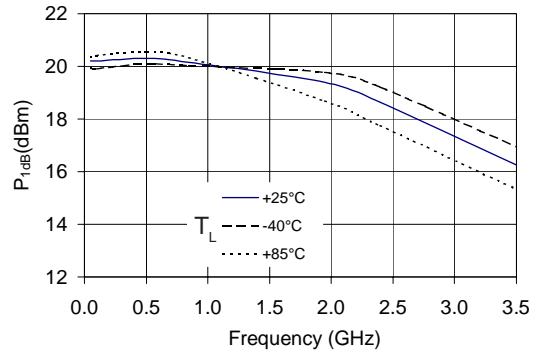
Bias Conditions should also satisfy the following expression:  
 $I_D V_D < (T_J - T_L) / R_{TH}, J-I$

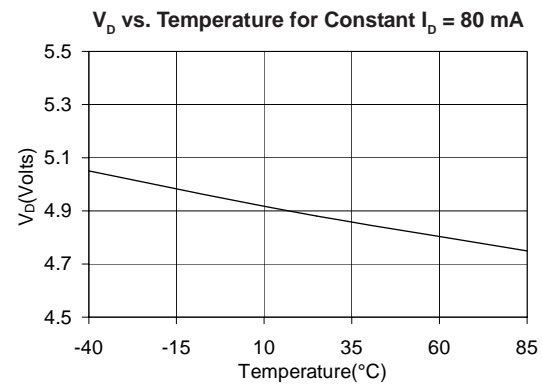
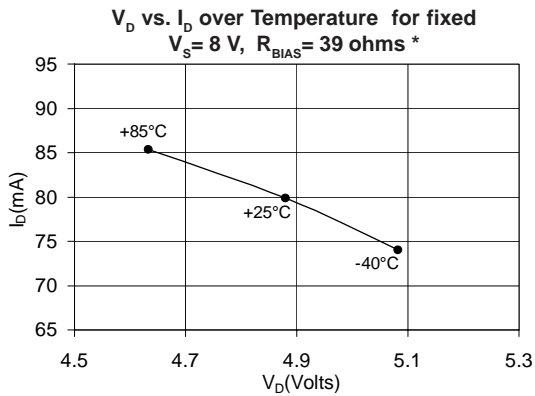
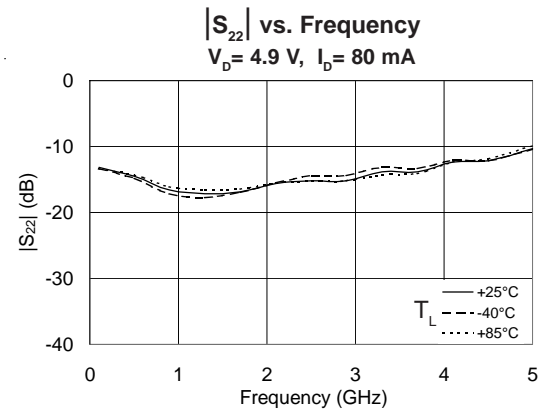
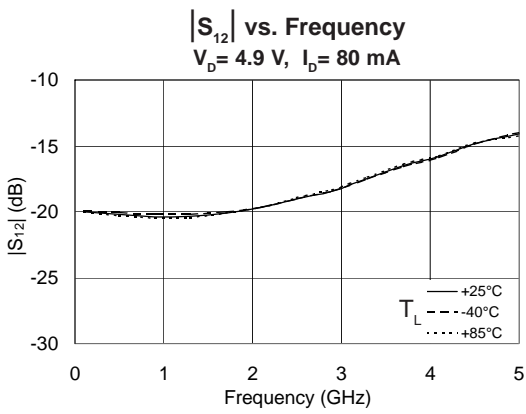
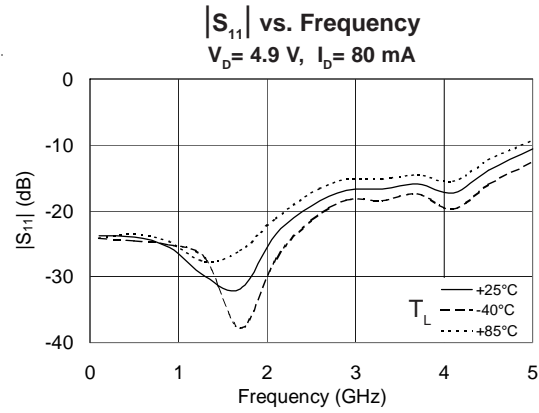
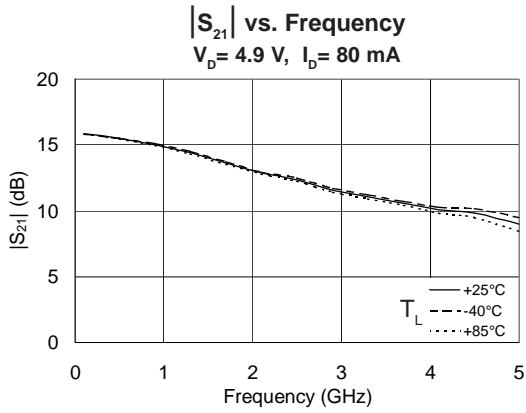
Take into account out of band VSWR presented by devices such as SAW filters to determine maximum RF input power. Reflected harmonic levels in saturation are significant.

**OIP<sub>3</sub> vs. Frequency**  
 $V_D = 4.9 V, I_D = 80 mA$



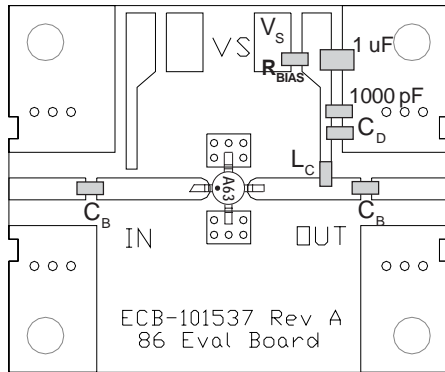
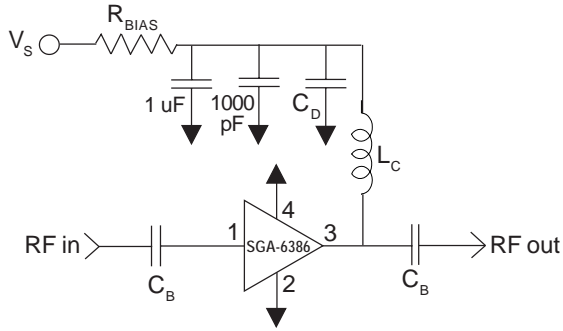
**P<sub>1dB</sub> vs. Frequency**  
 $V_D = 4.9 v, I_D = 80 mA$





\* Note: In the applications circuit on page 4,  $R_{BIAS}$  compensates for voltage and current variation over temperature.

**Basic Application Circuit**



**Application Circuit Element Values**

Reference Designator	Frequency (Mhz)				
	500	850	1950	2400	3500
C <sub>B</sub>	220 pF	100 pF	68 pF	56 pF	39 pF
C <sub>D</sub>	100 pF	68 pF	22 pF	22 pF	15 pF
L <sub>C</sub>	68 nH	33 nH	22 nH	18 nH	15 nH

**Recommended Bias Resistor Values for I<sub>D</sub>=80mA**  
 $R_{BIAS} = (V_S - V_D) / I_D$

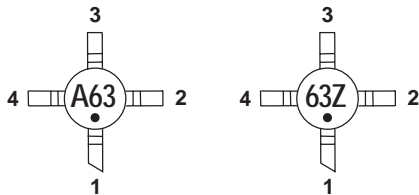
Supply Voltage(V <sub>S</sub> )	6 V	8 V	10 V	12 V
R <sub>BIAS</sub>	13 Ω	39 Ω	62 Ω	91 Ω

Note: R<sub>BIAS</sub> provides DC bias stability over temperature.

**Mounting Instructions**

1. Use a large ground pad area under device pins 2 and 4 with many plated through-holes as shown.
3. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

**Part Identification Marking**



Pin #	Function	Description
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
2, 4	GND	Connection to ground. For optimum RF performance, use via holes as close to ground leads as possible to reduce lead inductance.
3	RF OUT/BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.



**Caution: ESD sensitive**  
Appropriate precautions in handling, packaging and testing devices must be observed.

See Application Note AN-075  
for Package Outline Drawing

**Part Number Ordering Information**

Part Number	Reel Size	Devices/Reel
<b>SGA-6386</b>	<b>13"</b>	<b>3000</b>
<b>SGA-6386Z</b>	<b>13"</b>	<b>3000</b>